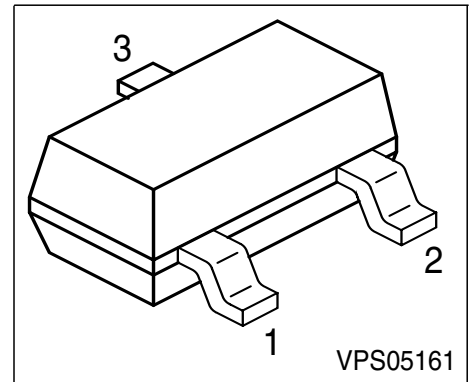


PNP Silicon AF Transistors

- For general AF applications
- High collector current
- High current gain
- Low collector-emitter saturation voltage
- Complementary types: BC 817, BC 818 (NPN)



Type	Marking	Pin Configuration			Package
BC 807-16	5As	1 = B	2 = E	3 = C	SOT-23
BC 807-25	5Bs	1 = B	2 = E	3 = C	SOT-23
BC 807-40	5Cs	1 = B	2 = E	3 = C	SOT-23
BC 808-16	5Es	1 = B	2 = E	3 = C	SOT-23
BC 808-25	5Fs	1 = B	2 = E	3 = C	SOT-23
BC 808-40	5Gs	1 = B	2 = E	3 = C	SOT-23

Maximum Ratings

Parameter	Symbol	BC 807	BC 808	Unit
Collector-emitter voltage	V_{CEO}	45	25	V
Collector-base voltage	V_{CBO}	50	30	
Emitter-base voltage	V_{EBO}	5	5	
DC collector current	I_C	500		mA
Peak collector current	I_{CM}	1		A
Base current	I_B	100		mA
Peak base current	I_{BM}	200		
Total power dissipation, $T_S = 79\text{ °C}$	P_{tot}	330		mW
Junction temperature	T_j	150		°C
Storage temperature	T_{stg}	-65 ... 150		

Thermal Resistance

Parameter	Symbol	BC 807	BC 808	Unit
Junction ambient ¹⁾	R_{thJA}	≤285		K/W
Junction - soldering point	R_{thJS}	≤215		

1) Package mounted on pcb 40mm x 40mm x 1.5mm / 6cm² Cu

Electrical Characteristics at $T_A = 25^\circ\text{C}$, unless otherwise specified.

Parameter	Symbol	Values			Unit	
		min.	typ.	max.		
DC Characteristics						
Collector-emitter breakdown voltage $I_C = 10\text{ mA}, I_B = 0$	$V_{(BR)CEO}$	BC 807	45	-	-	V
BC 808		25	-	-		
Collector-base breakdown voltage $I_C = 10\ \mu\text{A}, I_B = 0$	$V_{(BR)CBO}$	BC 807	50	-	-	
BC 808		30	-	-		
Emitter-base breakdown voltage $I_E = 10\ \mu\text{A}, I_C = 0$	$V_{(BR)EBO}$		5	-	-	
Collector cutoff current $V_{CB} = 25\text{ V}, I_E = 0$	I_{CBO}		-	-	100	nA
Collector cutoff current $V_{CB} = 25\text{ V}, I_E = 0, T_A = 150^\circ\text{C}$	I_{CBO}		-	-	50	μA
Emitter cutoff current $V_{EB} = 4\text{ V}, I_C = 0$	I_{EBO}		-	-	100	nA
DC current gain 1) $I_C = 100\text{ mA}, V_{CE} = 1\text{ V}$	h_{FE}	h_{FE} -grp. 16	100	160	250	-
		h_{FE} -grp. 25	160	250	400	
		h_{FE} -grp. 40	250	350	630	
DC current gain 1) $I_C = 300\text{ mA}, V_{CE} = 1\text{ V}$	h_{FE}	h_{FE} -grp. 16	60	-	-	
		h_{FE} -grp. 25	100	-	-	
		h_{FE} -grp. 40	170	-	-	
Collector-emitter saturation voltage1) $I_C = 500\text{ mA}, I_B = 50\text{ mA}$	V_{CEsat}		-	-	0.7	V
Base-emitter saturation voltage 1) $I_C = 500\text{ mA}, I_B = 50\text{ mA}$	V_{BEsat}		-	-	1.2	V

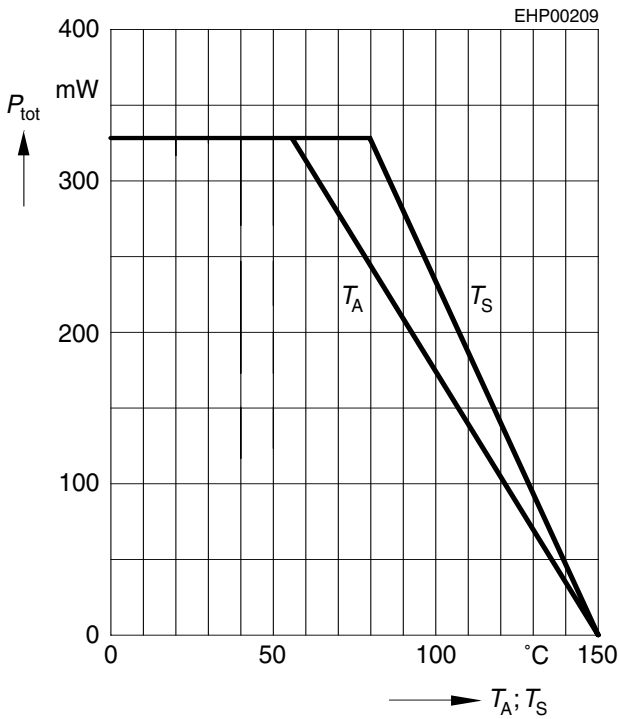
 1) Pulse test: $t \leq 300\ \mu\text{s}$, $D = 2\%$

Electrical Characteristics at $T_A = 25^\circ\text{C}$, unless otherwise specified.

Parameter	Symbol	Values			Unit
		min.	typ.	max.	
AC Characteristics					
Transition frequency $I_C = 50\text{ mA}$, $V_{CE} = 5\text{ V}$, $f = 100\text{ MHz}$	f_T	-	200	-	MHz
Collector-base capacitance $V_{CB} = 10\text{ V}$, $f = 1\text{ MHz}$	C_{cb}	-	10	-	pF
Emitter-base capacitance $V_{EB} = 0.5\text{ V}$, $f = 1\text{ MHz}$	C_{eb}	-	60	-	

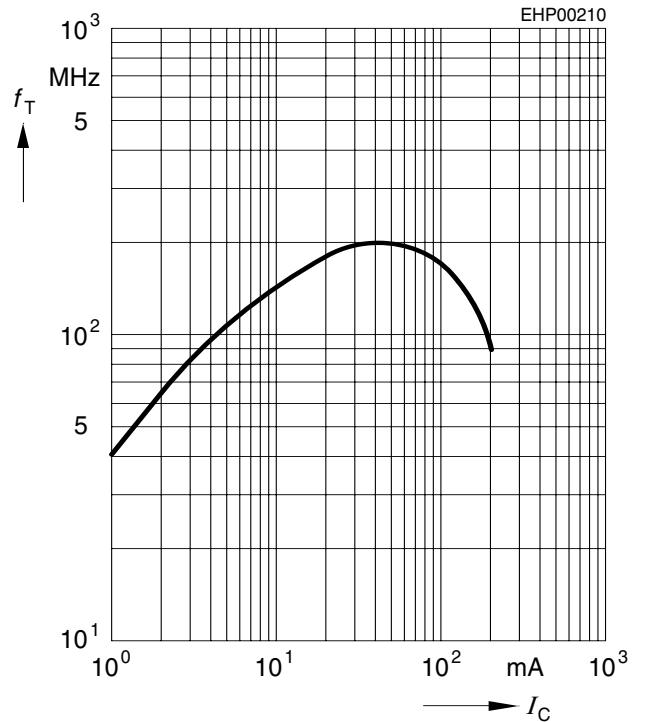
Total power dissipation $P_{tot} = f(T_A^*; T_S)$

* Package mounted on epoxy



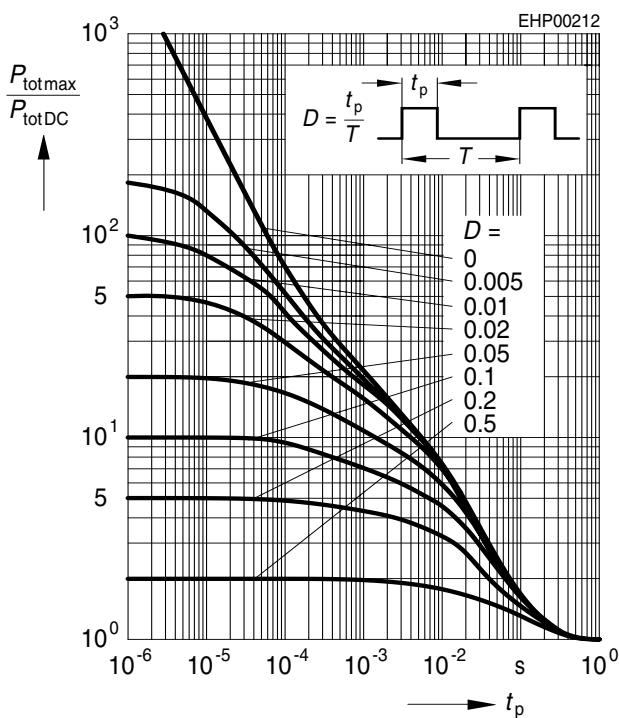
Transition frequency $f_T = f(I_C)$

$V_{CE} = 5V$



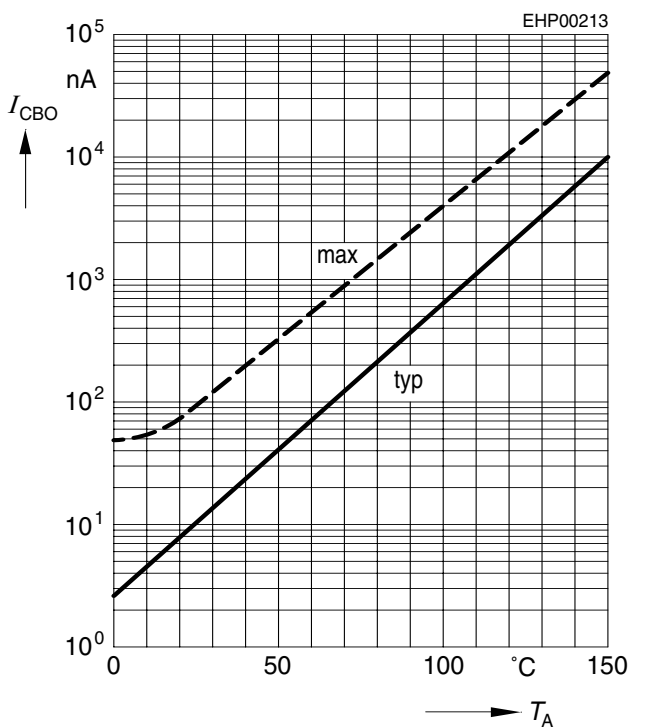
Permissible pulse load

$P_{totmax} / P_{totDC} = f(t_p)$



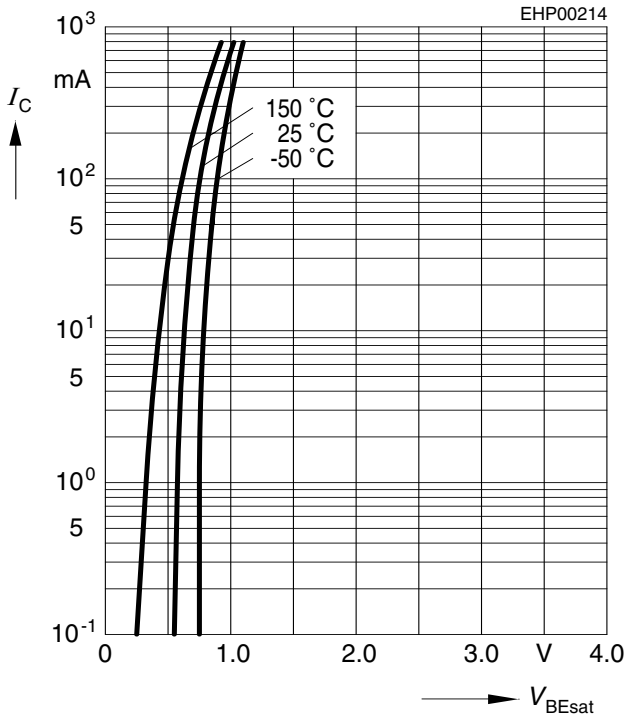
Collector cutoff current $I_{CBO} = f(T_A)$

$V_{CBO} = 25V$



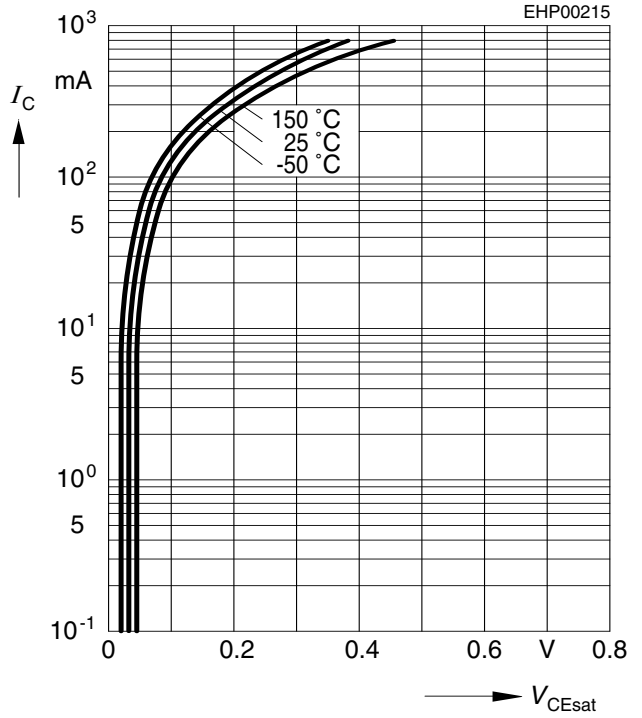
Base-emitter saturation voltage

$I_C = f(V_{BEsat}), h_{FE} = 10$



Collector-emitter saturation voltage

$I_C = f(V_{CEsat}), h_{FE} = 10$



DC current gain $h_{FE} = f(I_C)$

$V_{CE} = 1V$

